**Product data sheet** 

# 1. General description

N-channel enhancement mode Field-Effect Transistor (FET) in a leadless ultra small DFN1006-3 (SOT883) Surface-Mounted Device (SMD) plastic package using Trench MOSFET technology.

### 2. Features and benefits

- Trench MOSFET technology
- Low threshold voltage
- Very fast switching
- ElectroStatic Discharge (ESD) protection > 2 kV HBM
- Leadless ultra small SMD plastic package: 1.0 × 0.6 × 0.48 mm

## 3. Applications

- Relay driver
- · High-speed line driver
- Low-side loadswitch
- Switching circuits

### 4. Quick reference data

Table 1. Quick reference data

Symbol	Parameter	Conditions		Min	Тур	Max	Unit
$V_{DS}$	drain-source voltage	T <sub>j</sub> = 25 °C		-	-	30	V
$V_{GS}$	gate-source voltage			-8	-	8	V
I <sub>D</sub>	drain current	V <sub>GS</sub> = 4.5 V; T <sub>amb</sub> = 25 °C	[1]	-	-	900	mA
Static characteristics							
R <sub>DSon</sub>	drain-source on-state resistance	$V_{GS}$ = 4.5 V; $I_{D}$ = 500 mA; $T_{j}$ = 25 °C		-	370	490	mΩ

<sup>[1]</sup> Device mounted on an FR4 Printed-Circuit Board (PCB), single-sided copper, tin-plated, mounting pad for drain 1 cm<sup>2</sup>.





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# 5. Pinning information

### Table 2. Pinning information

Pin	Symbol	Description	Simplified outline	Graphic symbol
1	G	gate	1	D I
2	S	source	2 🔲 📗 3	
3	D	drain	Transparent top view  DFN1006-3 (SOT883)	G S 017aaa255

# 6. Ordering information

Table 3. Ordering information

Type number	Package					
	Name	Description	Version			
PMZ370UNE	DFN1006-3	DFN1006-3: leadless ultra small plastic package; 3 solder lands	SOT883			

# 7. Marking

Table 4. Marking codes

Type number	Marking code
PMZ370UNE	ZM

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# 8. Limiting values

Table 5. Limiting values

In accordance with the Absolute Maximum Rating System (IEC 60134).

Symbol	Parameter	Conditions		Min	Max	Unit
$V_{DS}$	drain-source voltage	T <sub>j</sub> = 25 °C		-	30	V
$V_{GS}$	gate-source voltage			-8	8	V
I <sub>D</sub>	drain current	V <sub>GS</sub> = 4.5 V; T <sub>amb</sub> = 25 °C	[1]	-	900	mA
		V <sub>GS</sub> = 4.5 V; T <sub>amb</sub> = 100 °C	[1]	-	560	mA
I <sub>DM</sub>	peak drain current	$T_{amb}$ = 25 °C; single pulse; $t_p \le 10 \mu s$		-	3.6	Α
P <sub>tot</sub>	total power dissipation	T <sub>amb</sub> = 25 °C	<u>[2]</u>	-	360	mW
			[1]	-	715	mW
		T <sub>sp</sub> = 25 °C		-	2700	mW
T <sub>j</sub>	junction temperature			-55	150	°C
T <sub>amb</sub>	ambient temperature			-55	150	°C
T <sub>stg</sub>	storage temperature			-65	150	°C
Source-drain	diode					-
I <sub>S</sub>	source current	T <sub>amb</sub> = 25 °C	[1]	-	680	mA
ESD maximu	m rating					,
V <sub>ESD</sub>	electrostatic discharge voltage	НВМ	[3]	-	2000	V

<sup>[1]</sup> Device mounted on an FR4 Printed-Circuit Board (PCB), single-sided copper, tin-plated, mounting pad for drain 1 cm<sup>2</sup>.

<sup>[2]</sup> Device mounted on an FR4 PCB, single-sided copper, tin-plated and standard footprint.

<sup>[3]</sup> Measured between all pins.

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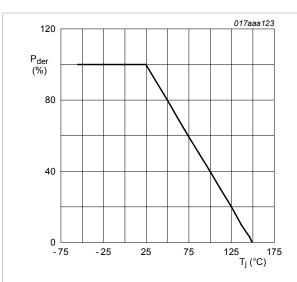


Fig. 1. Normalized total power dissipation as a function of junction temperature

$$P_{der} = \frac{P_{tot}}{P_{tot(25^{\circ}C)}} \times 100 \%$$

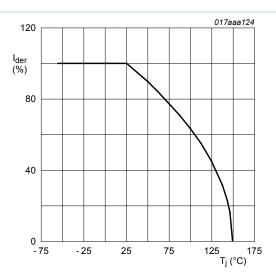


Fig. 2. Normalized continuous drain current as a function of junction temperature

$$I_{der} = \frac{I_D}{I_{D(25^{\circ}C)}} \times 100 \%$$

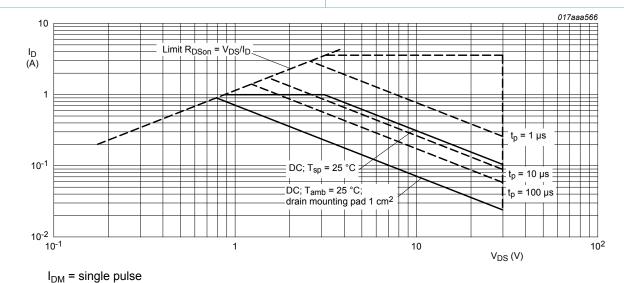


Fig. 3. Safe operating area; junction to ambient; continuous and peak drain currents as a function of drainsource voltage

### 9. Thermal characteristics

Table 6. Thermal characteristics

Symbol	Parameter	Conditions		Min	Тур	Max	Unit
R <sub>th(j-a)</sub>	thermal resistance	in free air	[1]	-	305	360	K/W
from	from junction to ambient		[2]	-	150	175	K/W

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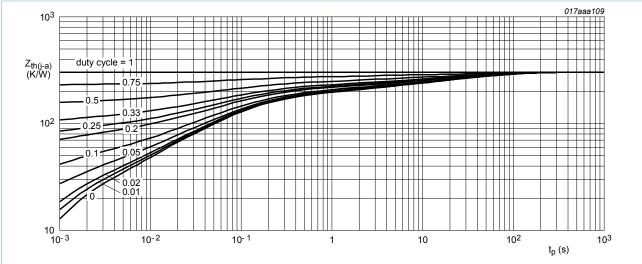
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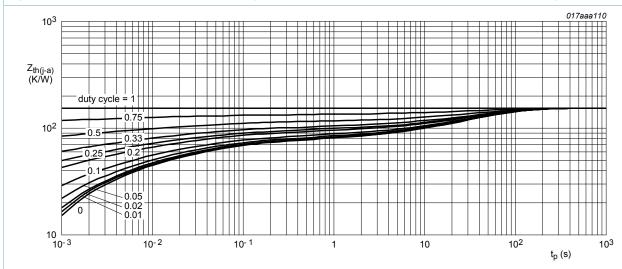
Symbol	Parameter	Conditions	Min	Тур	Max	Unit
R <sub>th(j-sp)</sub>	thermal resistance from junction to solder point		-	-	40	K/W

- [1] Device mounted on an FR4 PCB, single-sided copper, tin-plated and standard footprint.
- [2] Device mounted on an FR4 PCB, single-sided copper, tin-plated, mounting pad for drain 1 cm<sup>2</sup>.



FR4 PCB, standard footprint

Fig. 4. Transient thermal impedance from junction to ambient as a function of pulse duration; typical values



FR4 PCB, mounting pad for drain 1 cm<sup>2</sup>

Fig. 5. Transient thermal impedance from junction to ambient as a function of pulse duration; typical values

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# 10. Characteristics

### Table 7. Characteristics

Fable 7. Symbol	Characteristics Parameter	Conditions	Min	Typ	Max	Unit
		Conditions	IVIIII	Тур	IVIAX	Unit
	aracteristics					
V <sub>(BR)DSS</sub>	drain-source breakdown voltage	$I_D = 250 \mu A; V_{GS} = 0 V; T_j = 25 °C$	30	-	-	V
$V_{GSth}$	gate-source threshold voltage	$I_D = 250 \mu A; V_{DS} = V_{GS}; T_j = 25 \text{ °C}$	0.5	0.77	1.05	V
I <sub>DSS</sub>	drain leakage current	V <sub>DS</sub> = 30 V; V <sub>GS</sub> = 0 V; T <sub>j</sub> = 25 °C	-	-	1	μA
		V <sub>DS</sub> = 30 V; V <sub>GS</sub> = 0 V; T <sub>j</sub> = 150 °C	-	-	10	μA
I <sub>GSS</sub>	gate leakage current	V <sub>GS</sub> = 8 V; V <sub>DS</sub> = 0 V; T <sub>j</sub> = 25 °C	-	-	3	μA
		V <sub>GS</sub> = -8 V; V <sub>DS</sub> = 0 V; T <sub>j</sub> = 25 °C	-	-	3	μA
		V <sub>GS</sub> = -4.5 V; V <sub>DS</sub> = 0 V; T <sub>j</sub> = 25 °C	-	-	0.5	μA
		V <sub>GS</sub> = 4.5 V; V <sub>DS</sub> = 0 V; T <sub>j</sub> = 25 °C	-	-	0.5	μA
R <sub>DSon</sub>	drain-source on-state	$V_{GS}$ = 4.5 V; $I_D$ = 500 mA; $T_j$ = 25 °C	-	370	490	mΩ
	resistance	V <sub>GS</sub> = 4.5 V; I <sub>D</sub> = 500 mA; T <sub>j</sub> = 150 °C	-	650	860	mΩ
		$V_{GS} = 2.5 \text{ V}; I_D = 400 \text{ mA}; T_j = 25 ^{\circ}\text{C}$	-	470	750	mΩ
		$V_{GS}$ = 1.8 V; $I_{D}$ = 100 mA; $T_{j}$ = 25 °C	-	630	1300	mΩ
9 <sub>fs</sub>	forward transconductance	$V_{DS}$ = 10 V; $I_{D}$ = 200 mA; $T_{j}$ = 25 °C	-	1580	-	mS
Dynamic	characteristics		l	1		
Q <sub>G(tot)</sub>	total gate charge	V <sub>DS</sub> = 15 V; I <sub>D</sub> = 500 mA; V <sub>GS</sub> = 4.5 V;	-	0.77	1.16	nC
Q <sub>GS</sub>	gate-source charge	T <sub>j</sub> = 25 °C	-	0.15	-	nC
$Q_{GD}$	gate-drain charge		-	0.16	-	nC
C <sub>iss</sub>	input capacitance	V <sub>DS</sub> = 25 V; f = 1 MHz; V <sub>GS</sub> = 0 V;	-	52	78	pF
C <sub>oss</sub>	output capacitance	T <sub>j</sub> = 25 °C	-	9	-	pF
C <sub>rss</sub>	reverse transfer capacitance		-	3	-	pF
t <sub>d(on)</sub>	turn-on delay time	$V_{DS}$ = 15 V; $R_L$ = 250 $\Omega$ ; $V_{GS}$ = 4.5 V;	-	11	22	ns
t <sub>r</sub>	rise time	$R_{G(ext)} = 6 \Omega; T_j = 25 ^{\circ}C$	-	9	-	ns
$t_{d(off)}$	turn-off delay time		-	54	108	ns
t <sub>f</sub>	fall time		-	27	-	ns
Source-d	rain diode		ı		'	,
V <sub>SD</sub>	source-drain voltage	I <sub>S</sub> = 300 mA; V <sub>GS</sub> = 0 V; T <sub>j</sub> = 25 °C	0.48	0.76	1.2	V

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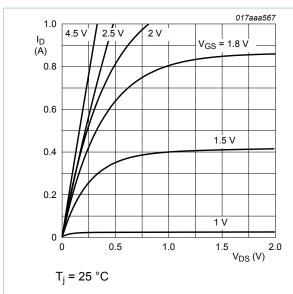


Fig. 6. Output characteristics: drain current as a function of drain-source voltage; typical values

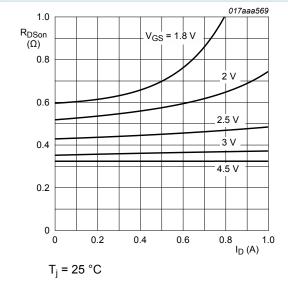


Fig. 8. Drain-source on-state resistance as a function of drain current; typical values

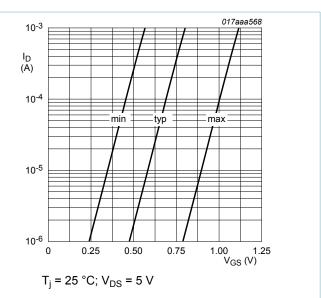


Fig. 7. Sub-threshold drain current as a function of gate-source voltage

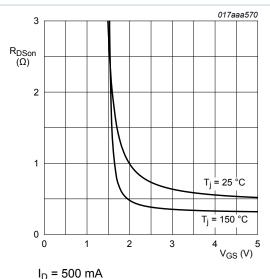


Fig. 9. Drain-source on-state resistance as a function of gate-source voltage; typical values

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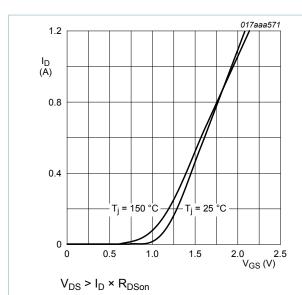


Fig. 10. Transfer characteristics: drain current as a function of gate-source voltage; typical values

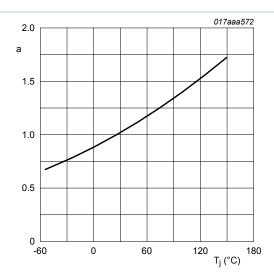


Fig. 11. Normalized drain-source on-state resistance as a function of junction temperature; typical values

$$a = \frac{R_{DSon}}{R_{DSon(25^{\circ}C)}}$$

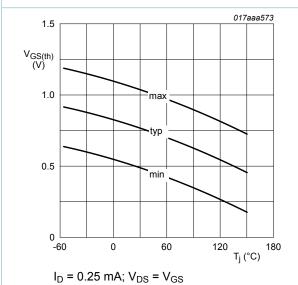
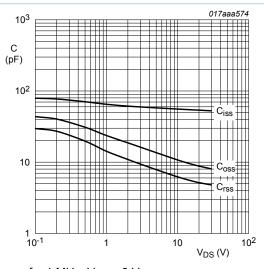


Fig. 12. Gate-source threshold voltage as a function of junction temperature



 $f = 1 MHz; V_{GS} = 0 V$ 

Fig. 13. Input, output and reverse transfer capacitances as a function of drain-source voltage; typical values

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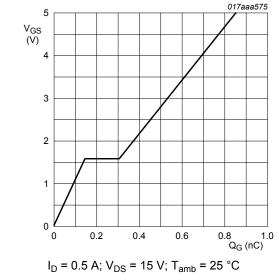


Fig. 14. Gate-source voltage as a function of gate

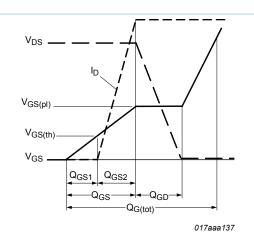


Fig. 15. Gate charge waveform definitions

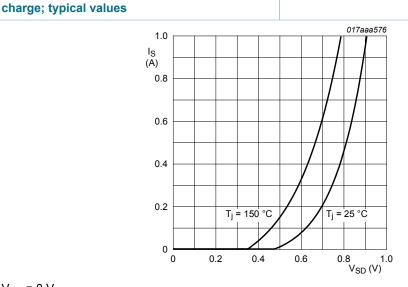
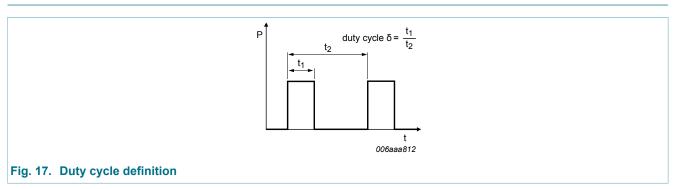


Fig. 16. Source current as a function of source-drain voltage; typical values

## 11. Test information

 $V_{GS} = 0 V$ 



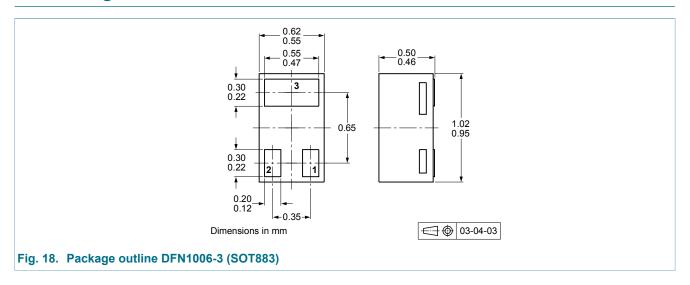
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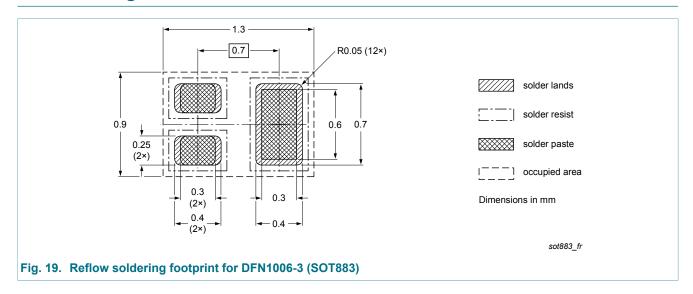
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# 12. Package outline



# 13. Soldering



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# 14. Revision history

### Table 8. Revision history

Data sheet ID	Release date	Data sheet status	Change notice	Supersedes
PMZ370UNE v.1	20140514	Product data sheet	-	-

#### 30 V, N-channel Trench MOSFET

## 15. Legal information

#### 15.1 Data sheet status

Document status [1][2]	Product status [3]	Definition
Objective [short] data sheet	Development	This document contains data from the objective specification for product development.
Preliminary [short] data sheet	Qualification	This document contains data from the preliminary specification.
Product [short] data sheet	Production	This document contains the product specification.

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